

April 2013.
PRELIMINARY.

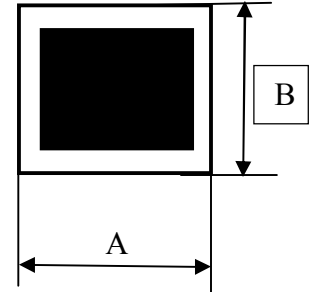
SM-7N.

Chip TVS diode.

Die size: 22,8*15,4mil.

Mechanical date: A= 580um; B=390um. Chip thickness –230+/-20um.
Scribe Line Width – 60um.
Top side – Anode. Al metallization for wire bond.

Back side- Cathode. Metallization Ti- Ni-Ag for soldering.



Limiting values

Parameter	Symbol	Conditions	Value	Unit
Working Peak Reverse Voltage	V_{RWM}		7,0.	V
Peak Pulse Power	P_{pp}	$t_p = 8/20\mu S$	180*	W
Max. Peak Pulse Current	I_{pp}	$t_p = 8/20\mu S$	17,0*	A
Electrostatic discharge	V_{ESD}	IEC 61000-4-2. Level-4.	+/-8,0 – Contact. +/-15,0 – Air.	kV
Max.Junction Temperature	T_j		+150	°C

Characteristics . $T_j=25^\circ C$.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_R	Diode reverse leakage current.	$V_R=7,0V$	-	-	5,0	uA
V_{BR}	Breakdown voltage.	$I_R=1mA$	7,0	-	8,8	V
C_j	Diode capacitance .	$F=1MHz, V_R=0 V$.	-	180	200	pF
V_{CL}	Clamping voltage	$I_R=5A, t_p= 8/20\mu S$ $I_R= 17A, t_p= 8/20\mu S$	-	-	9,3* 10,5*	V

*- For Device testing.